

ABSTRACT OF THE DISCLOSURE

In a semiconductor device and a method of manufacturing the same according to the present invention, a trade-off relationship between threshold values and a diffusion layer ^{leakage} ~~leak~~ is eliminated and it is not necessary to form gate oxide films at more than one stages. Since doses of nitrogen are different from each other between gate electrodes (4A to 4C) of N-channel type MOS transistors (T41 to T43), concentrations of nitrogen in the nitrogen-introduced regions (N1 to N3) are accordingly different from each other. Concentrations of nitrogen in the gate electrodes are progressively lower in the order of expected higher threshold values.

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